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FDS4559

60V Complementary PowerTrench®MOSFET

General Description

This complementary MOSFET device is produced using Fairchild's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

Applications

- DC/DC converter
- · Power management
- LCD backlight inverter

Features

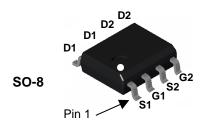
Q1: N-Channel

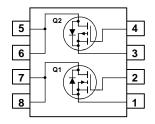
4.5 A, 60 V
$$R_{DS(on)} = 55 \ m\Omega \ @ \ V_{GS} = 10V$$

$$R_{DS(on)} = 75 \ m\Omega \ @ \ V_{GS} = 4.5V$$

Q2: P-Channel

$$-3.5$$
 A, -60 V R_{DS(on)} = 105 m Ω @ V_{GS} = -10 V
$$R_{DS(on)} = 135$$
 m Ω @ V_{GS} = -4.5 V





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

| Symbol | Parameter | | Q1 | Q2 | Units |
|-----------------------------------|--|------------|--------|------|-------|
| V _{DSS} | Drain-Source Voltage | | 60 | -60 | V |
| V _{GSS} | Gate-Source Voltage | | ±20 | ±20 | V |
| I _D | Drain Current - Continuous | (Note 1a) | 4.5 | -3.5 | Α |
| | - Pulsed | | 20 | -20 | |
| P _D | Power Dissipation for Dual Operation | | 2 | W | |
| | Power Dissipation for Single Operation | (Note 1a) | 1. | 6 | |
| | | (Note 1b) | 1. | 2 | |
| | | (Note 1c) | 1 | | |
| T _J , T _{STG} | Operating and Storage Junction Tempera | ture Range | -55 to | +175 | °C |

Thermal Characteristics

| R _{θJA} | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 78 | °C/W |
|------------------|---|-----------|----|------|
| R _{θJC} | Thermal Resistance, Junction-to-Case | (Note 1) | 40 | °C/W |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|---------|-----------|------------|------------|
| FDS4559 | FDS4559 | 13" | 12mm | 2500 units |

| Symbol | Parameter | Test Conditions | Туре | Min | Тур | Max | Units |
|---------------------|--|--|----------|-----|------------|--------------|-----------|
| Drain-S | ource Avalanche Rating |]S (Note 1) | | | | | |
| W _{DSS} | Single Pulse Drain-Source Avalanche Energy | $V_{DD} = 30 \text{ V}, \qquad I_{D} = 4.5 \text{ A}$ | Q1 | | | 90 | mJ |
| I _{AR} | Maximum Drain-Source Avalanche Current | | Q1 | | | 4.5 | Α |
| Off Cha | racteristics | | | | | | |
| BV _{DSS} | Drain-Source Breakdown | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | Q1 | 60 | | | V |
| . 5) (| Voltage | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | Q2 | -60 | | | 1400 |
| <u>ΔBVdss</u> | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced to 25°C | Q1 Q2 | | 58 –49 | | mV/°C |
| ΔT _J | Zero Gate Voltage Drain | $I_D = -250 \mu A$, Referenced to 25°C $V_{DS} = 48 \text{ V}$, $V_{GS} = 0 \text{ V}$ | Q2 Q1 | | -49 | 1 | |
| I _{DSS} | Current | $V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$ | Q1 Q2 | | | 1 -1 | μΑ |
| I _{GSS} | Gate-Body Leakage | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | Q1 | | | +100 | nA |
| -000 | The state of the s | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | Q2 | | | <u>+</u> 100 | |
| On Cha | racteristics (Note 2) | | | | • | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | Q1 | 1 | 2.2 | 3 | V |
| - 00(11) | | $V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$ | Q2 | -1 | -1.6 | -3 | |
| $\Delta V_{GS(th)}$ | Gate Threshold Voltage | I _D = 250 μA, Referenced to 25°C | Q1 | | -5.5 | | mV/°C |
| ΔT_J | Temperature Coefficient | $I_D = -250 \mu A$, Referenced to $25^{\circ}C$ | Q2 | | 4 | | |
| $R_{DS(on)}$ | Static Drain-Source | $V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}$ | Q1 | | 42 | 55 | $m\Omega$ |
| | On-Resistance | $V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}, T_J = 125^{\circ}\text{C}$ | | | 72 | 94 | |
| | | $V_{GS} = 4.5 \text{ V}, I_D = 4 \text{ A}$ $V_{GS} = -10 \text{ V}, I_D = -3.5 \text{ A}$ | 00 | | 55 | 75 | |
| | | | Q2 | | 82 | 105 | |
| | | $V_{GS} = -10 \text{ V}, I_D = -3.5 \text{ A}, T_J = 125^{\circ}\text{C}$ | | | 130 105 | 190 135 | |
| <u> </u> | On-State Drain Current | $V_{GS} = -4.5 \text{ V}, I_D = -3.1 \text{ A}$ $V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$ | Q1 | 20 | 105 | 133 | Α |
| I _{D(on)} | On-State Diam Current | $V_{GS} = 10 \text{ V}, V_{DS} = 3 \text{ V}$ $V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$ | Q2 | -20 | | | ^ |
| g _{FS} | Forward Transconductance | $V_{DS} = 10 \text{ V}, I_{D} = 4.5 \text{ A}$ | Q1 | | 14 | | S |
| | | $V_{DS} = -5 \text{ V}, I_{D} = -3 \text{ 5 A}$ | Q2 | | 9 | | |
| Dvnami | ic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | Q1 | Q1 | | 650 | | pF |
| - 133 | | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ | Q2 | | 759 | | - |
| Coss | Output Capacitance | f = 1.0 MHz | Q1 | | 80 | | pF |
| | | Q2 | Q2 | | 90 | | |
| C _{rss} | Reverse Transfer | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V},$ | Q1 | | 35 | | pF |
| | Capacitance | f = 1.0 MHz | Q2 | | 39 | | |
| Switchin | g Characteristics (Note 2 |) | | | | | |
| | Turn-On Delay Time | Q1 | Q1 | | 11 | 20 | ns |
| (011) | , | $V_{DD} = 30 \text{ V}, I_D = 1 \text{ A},$ | Q2 | | 7 | 14 | |
| | Turn-On Rise Time | $V_{GS} = 10V$, $R_{GEN} = 6 \Omega$ | Q1 | | 8 | 18 | ns |
| | | | Q2 | | 10 | 20 | |
| d(off) | Turn-Off Delay Time | Q2 $V_{DD} = -30 \text{ V}, I_{D} = -1 \text{ A},$ | Q1 | | 19 | 35 | ns |
| | Turn-Off Fall Time | $V_{GS} = -30 \text{ V}, I_D = -1 \text{ A},$ $V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$ | Q2 | | 19 6 | 34 15 | no |
| | Tulli-Oil Fall Tillie | VGS = 10 V, NGEN = 0 22 | Q1 Q2 | | 12 | 22 | ns |
| Q_g | Total Gate Charge | Q1 | Q1 | | 12.5 | 18 | nC |
| | _ | $V_{DS} = 30 \text{ V}, I_D = 4.5 \text{ A}, V_{GS} = 10 \text{ V}$ | Q2 | | 15 | 21 | |
|) _{gs} | Gate-Source Charge | | Q1 | | 2.4 | | nC |
| | | Q2 | Q2 | | 2.5 | | |
|) gd | Gate-Drain Charge | $V_{DS} = -30 \text{ V}, I_{D} = -3.5 \text{ A}, V_{GS} = -10 \text{V}$ | Q1 | | 2.6 | | nC |
| | | | Q2 | | 3.0 | | 1 |

Electrical Characteristics (continued) T_A = 25°C unless otherwise noted

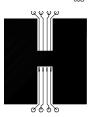
| Symbol | Parameter | Test Conditions | Туре | Min | Тур | Max | Units |
|--------|-----------|-----------------|------|-----|-----|-----|-------|
| | | | | | | | |

Drain-Source Diode Characteristics and Maximum Ratings

| Is | Maximum Continuous Drain-Source Diode Forward Current | | Q1 Q2 | | 1.3 –1.3 | Α |
|----------|---|---|----------|-------------|-------------|---|
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_{S} = 1.3 \text{ A} \text{ (Note 2)}$ $V_{GS} = 0 \text{ V}, I_{S} = -1.3 \text{ A} \text{ (Note 2)}$ | Q1 Q2 | 0.8 -0.8 | 1.2 –1.2 | V |

Notes

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in² pad of 2 oz copper



b) 125°C/W when mounted on a .02 in² pad of 2 oz copper



c) 135°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

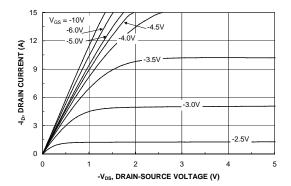


Figure 1. On-Region Characteristics.

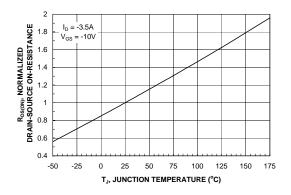


Figure 3. On-Resistance Variation with Temperature.

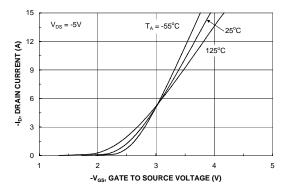


Figure 5. Transfer Characteristics.

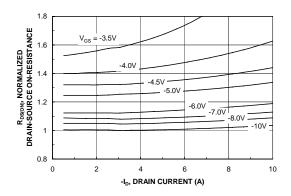


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

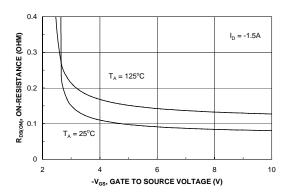


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

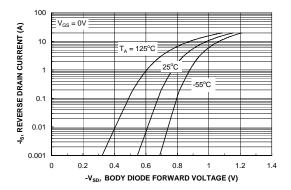


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

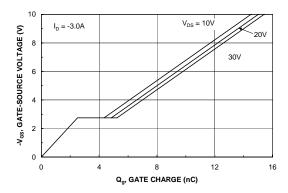


Figure 7. Gate Charge Characteristics.

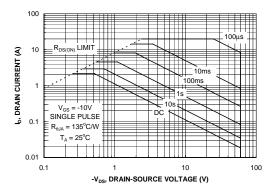


Figure 9. Maximum Safe Operating Area.

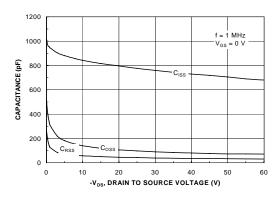


Figure 8. Capacitance Characteristics.

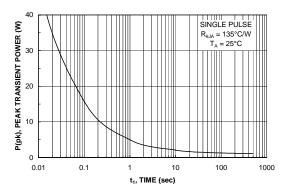


Figure 10. Single Pulse Maximum Power Dissipation.

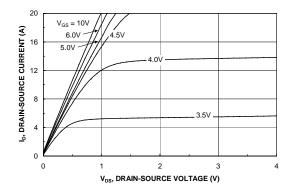


Figure 11. On-Region Characteristics.

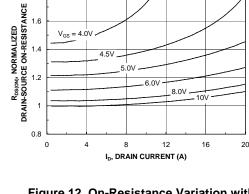


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

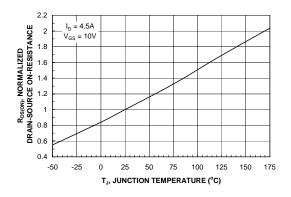


Figure 13. On-Resistance Variation with Temperature.

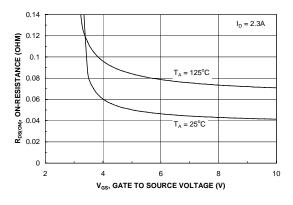


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

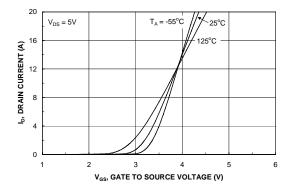


Figure 15. Transfer Characteristics.

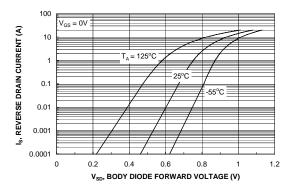
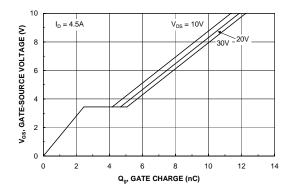


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.



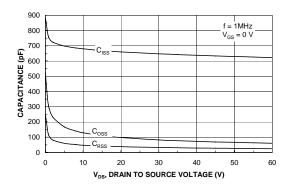
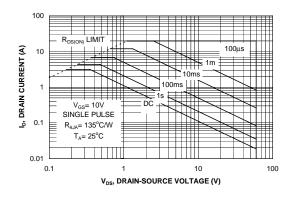


Figure 17. Gate Charge Characteristics.





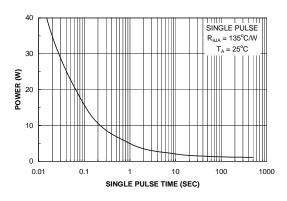


Figure 19. Maximum Safe Operating Area.

Figure 20. Single Pulse Maximum Power Dissipation.

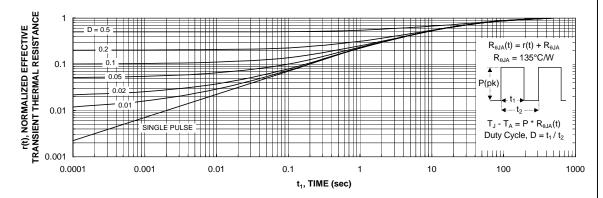


Figure 21. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.





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